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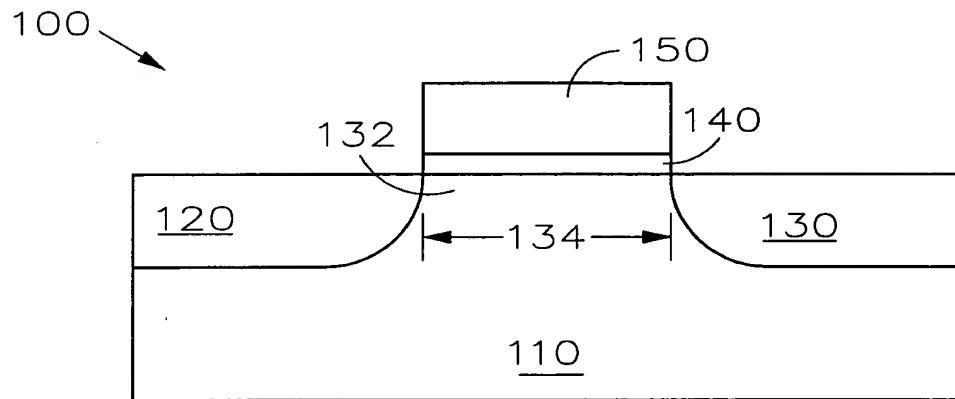


Fig. 1

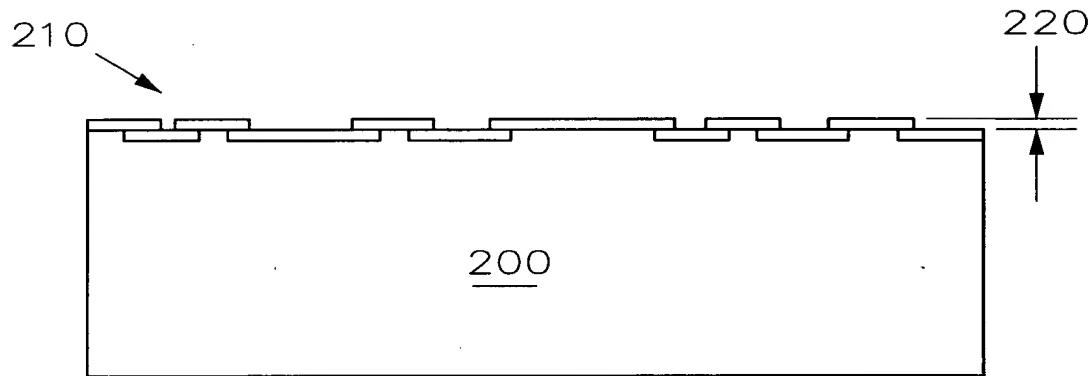


Fig. 2a

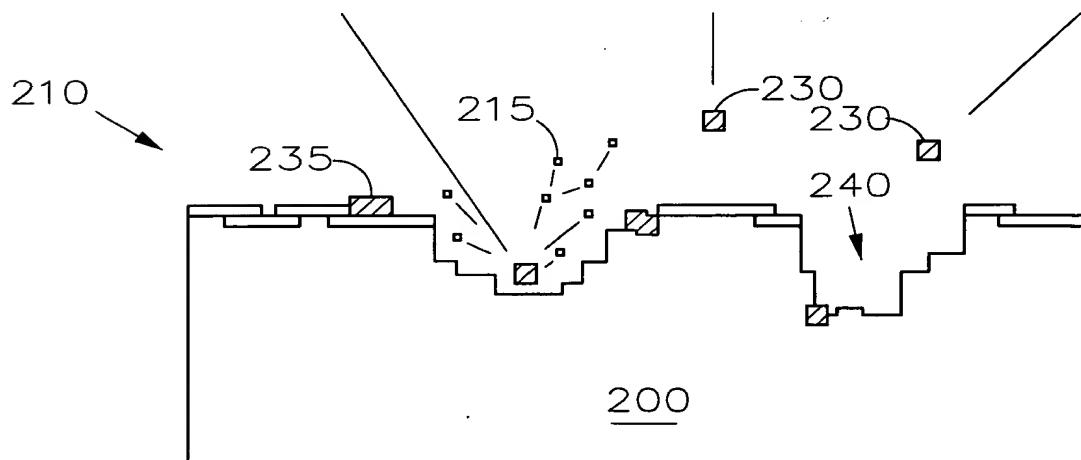


Fig. 2b

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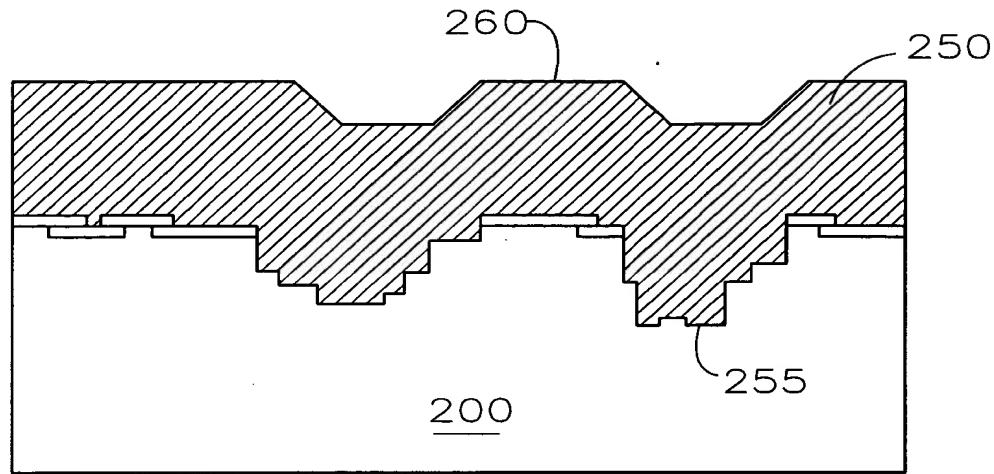


Fig. 2c

260 250 255 200

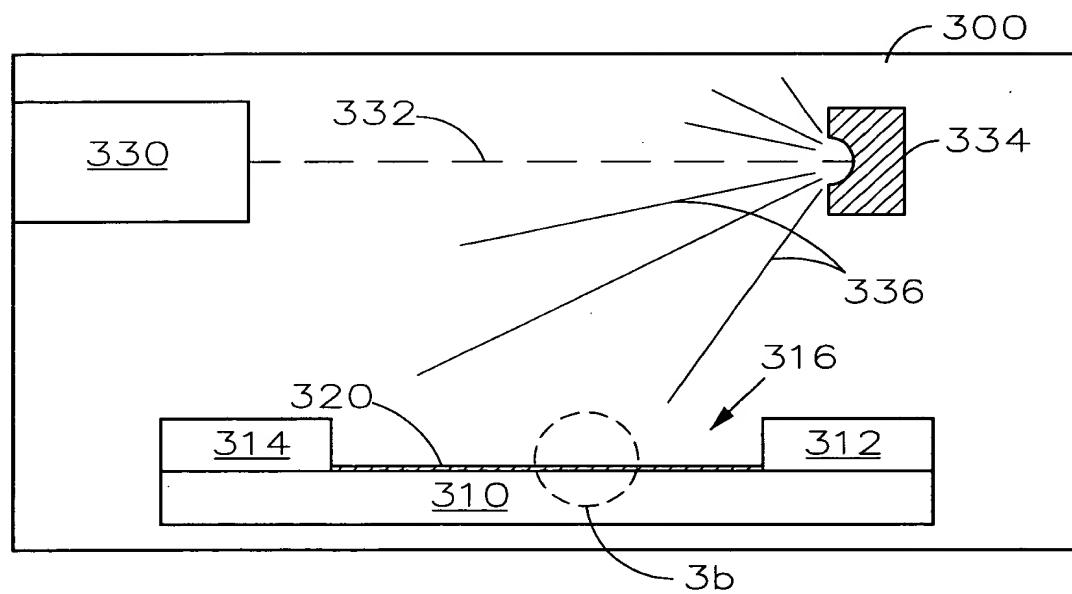


Fig. 3a

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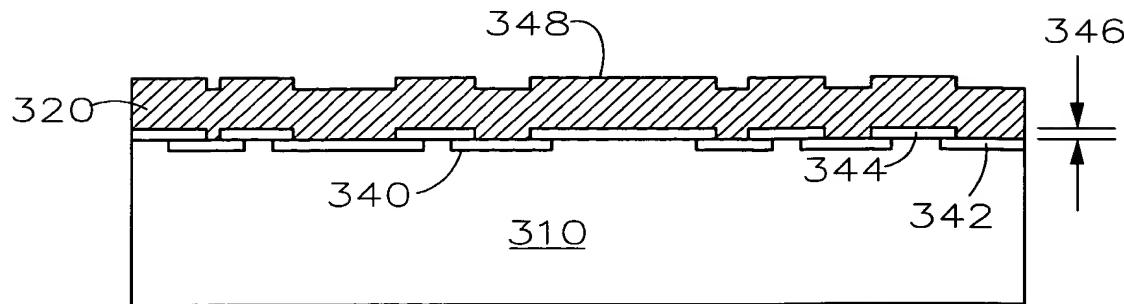


Fig. 3b

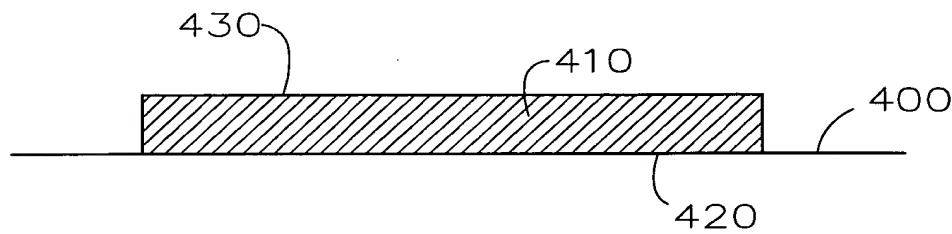


Fig. 4a

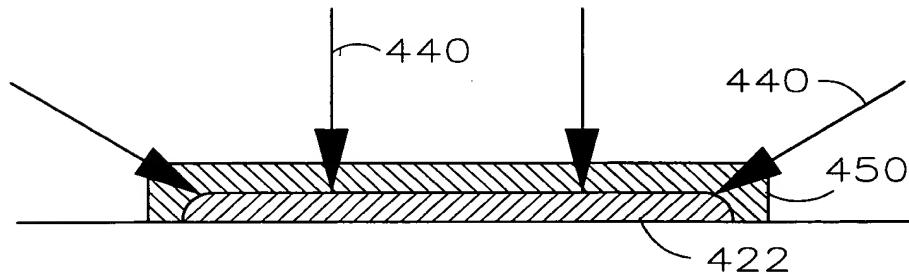


Fig. 4b

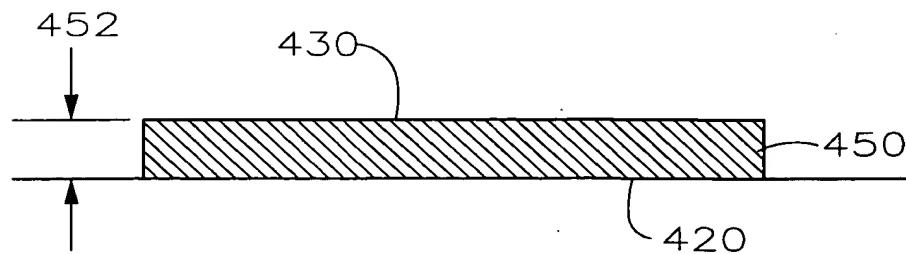


Fig. 4c

THE HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE  
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DOCKET NO.: 1303.026US1

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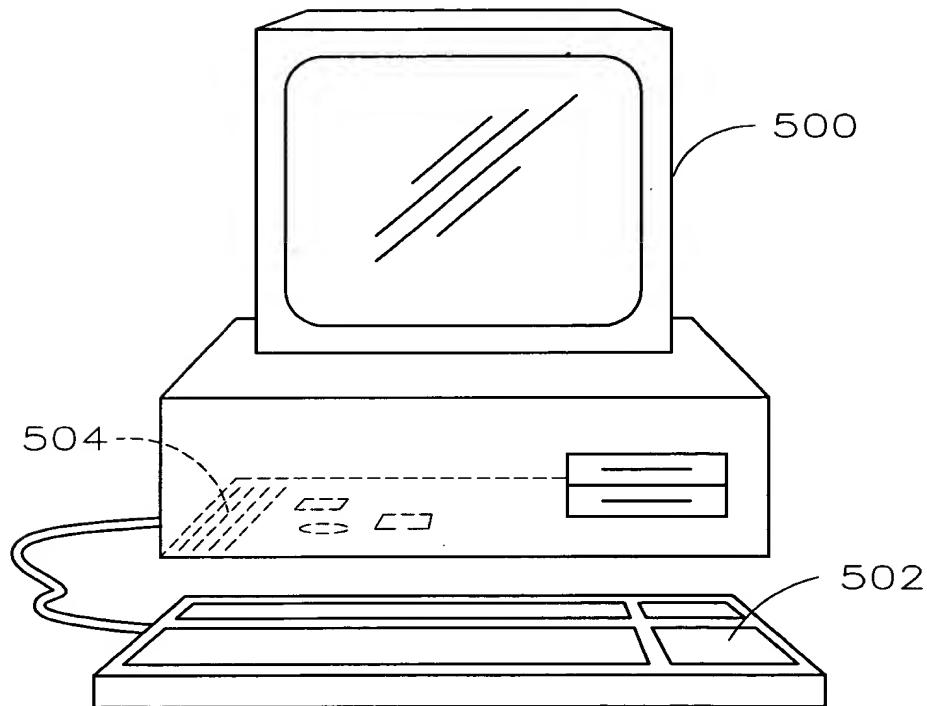


Fig. 5

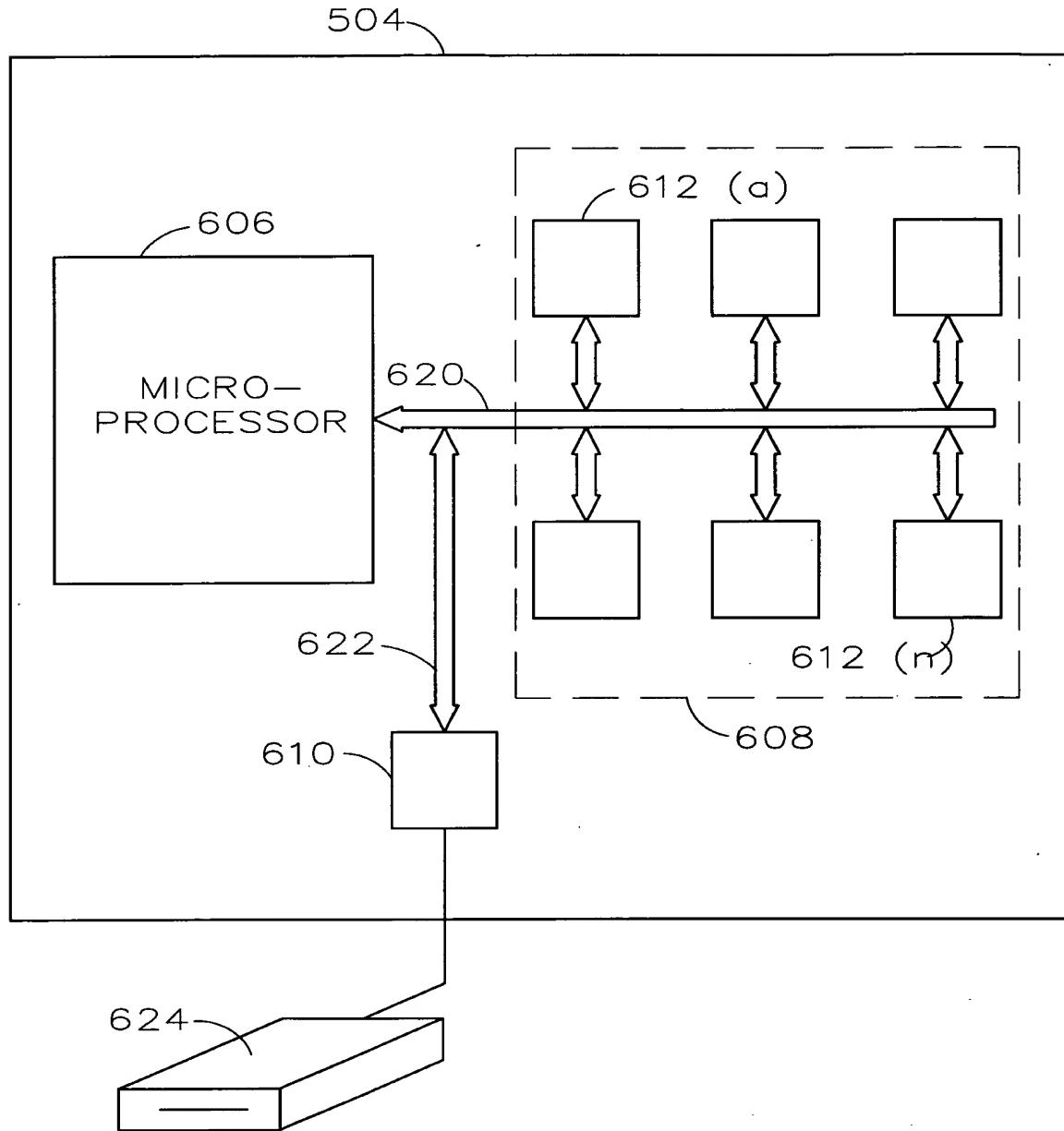


Fig. 6

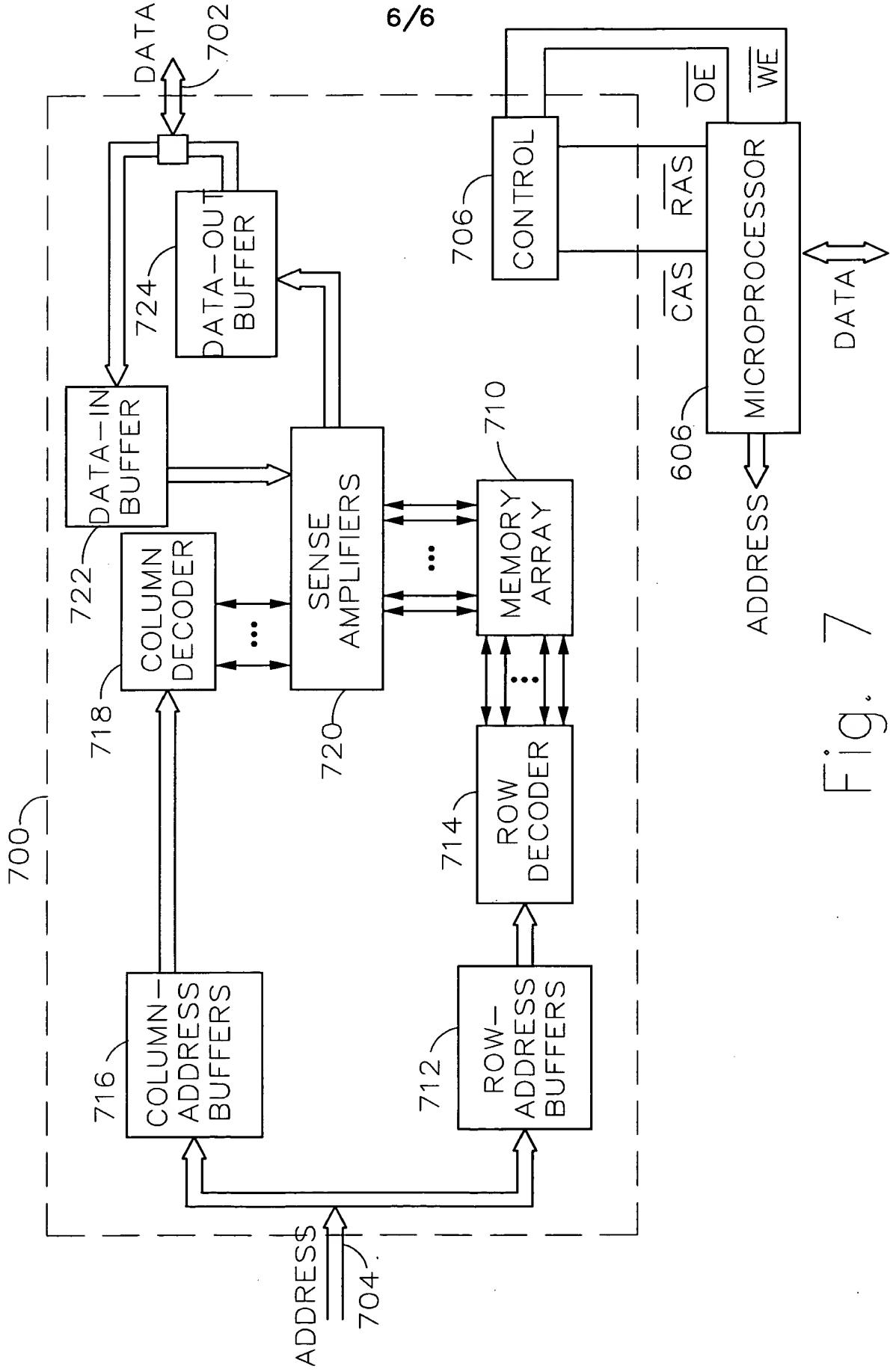


Fig. 7